

SIDC02D65C8

Fast switching diode chip in EMCON 3 -Technology

Features:

- 650V EMCON 3 technology 65 µm chip
- Soft, fast switching
- Low reverse recovery charge
- Small temperature coefficient
- Qualified according to JEDEC for target applications

Recommended for:

- Power module
- Discrete components



Applications:

- Drives
- White goods
- Resonant applications

Chip Type	V_{R}	<i>I</i> _{Fn} ¹⁾	Die Size	Package
SIDC02D65C8	650V	6A	1.4 x 1.65 mm ²	sawn on foil

nominal forward current at Tc = 100°C, not subject to production test - verified by design/characterisation

Mechanical Parameters

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Die size		1.4 x 1.65		
Area total		2.31	mm ²	
Anode pad size		0.97 x 1.22		
Thickness		65	μm	
Wafer size		200	mm	
Max. possible chips pe	er wafer	12228		
Passivation frontside		Photoimide		
Pad metal		3200 nm AlSiCu		
Backside metal		Ni Ag –system		
Die bond		Electrically conductive epoxy glue and soft solder		
Wire bond		Al, ≤500μm		
Reject ink dot size		Ø 0.65mm; max 1.2mm		
Storage environment	for original and sealed MBB bags	Ambient atmosphere air, Temperature 17°C – 25°C < 6 month		
	for open MBB bags	Acc. to IEC62258-3: Atmosphere >99% Nitrogen or Humidity <25%RH, Temperature 17°C – 25°C, <		



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Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V _{RRM}	T _{vj} = 25 °C	650	V
Continuous forward current	I _F	<i>T</i> _{vj} < 150°C	1)	
Maximum repetitive forward current ²⁾	IFRM	<i>T</i> _{vj} < 150°C	12	Α
Operating junction temperature	T _{vj}		-40+175	°C

¹⁾ depending on thermal properties of assembly

Static Characteristics (tested on wafer), T_{vj} = 25 °C

Parameter	Symbol Condi	Conditions	Value			Unit
- raiailletei		Conditions	min.	typ.	max.	Oilit
Reverse leakage current	I_{R}	V _R =650V			0.1	μA
Cathode-Anode breakdown Voltage	V _{BR}	I _R =0.25mA	650			V
Forward voltage drop	V _F	/ _F =6A	1.23	1.55	1.87	

Electrical Characteristics (not subject to production test - verified by design/characterization)

Parameter	Symbol	Conditions	Value			Unit
- raiailletei	Syllibol	Conditions	min.	typ.	max.	Oiiit
Forward voltage drop	V _F	$I_{\rm F}$ =6A, $T_{\rm vj}$ = 150°C		1.5		V

Further Electrical Characteristics

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

This chip data sheet refers to the device data sheet	tbd	tbd
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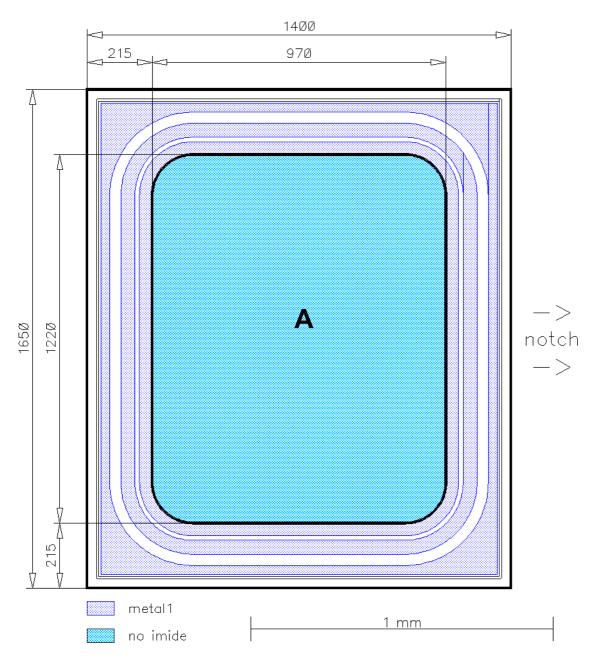
²⁾ not subject to production test - verified by design/characterisation





Chip Drawing

Die-Size 1400 um x 1650 um



A: Anode pad



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Description
AQL 0,65 for visual inspection according to failure catalogue
Electrostatic Discharge Sensitive Device according to MIL-STD 883

Revision History

Version	Subjects (major changes since last revision)	Date

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Information

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